

## 2SD1802 TRANSISTOR (NPN)

### FEATURES

- Adoption of FBET,MBIT Processes
- Large Current Capacity and Wide ASO
- Low Collector-to-Emitter Saturation Voltage
- Fast Switching Speed



### MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current –Continuous	3	A
P <sub>C</sub>	Collector Power Dissipation	1	W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55-150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10mA, I <sub>E</sub> = 0	60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0	50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10mA, I <sub>C</sub> = 0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 40V, I <sub>E</sub> = 0			1	mA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V, I <sub>C</sub> = 0			1	mA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = 2V, I <sub>C</sub> = 100mA	100		560	
	h <sub>FE(2)</sub>	V <sub>CE</sub> = 2V, I <sub>C</sub> = 3A	35			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 2A, I <sub>B</sub> = 100mA			0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 2A, I <sub>B</sub> = 100mA			1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 50mA		150		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz		25		pF

### CLASSIFICATION OF h<sub>FE(1)</sub>

Rank	R	S	T	U
Range	100-200	140-280	200-400	280-560

